

DUAL N-CANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Product Summary

BV _{DSS}	R _{DS(on)} Max	I _D Max T _A = +25°C
60V	3Ω @ V _{GS} = 5V	0.3A

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface-Mount Package
- ESD Protected up to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet (DMN601DWKQ)**

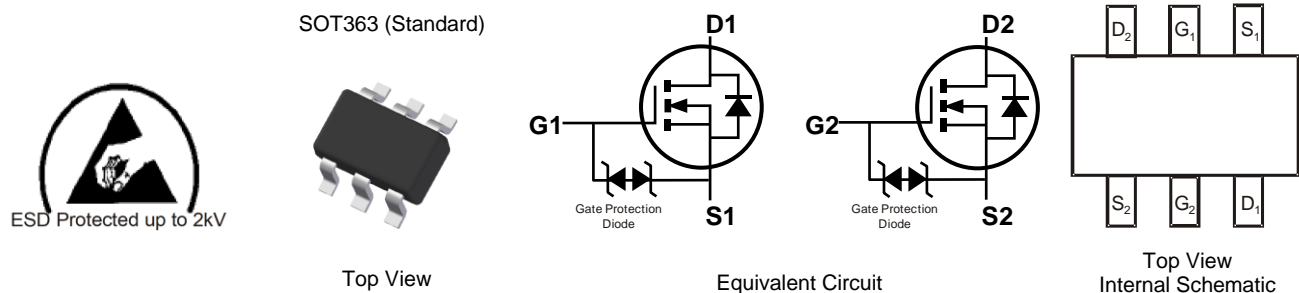
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Power-management functions

Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 Ⓔ
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

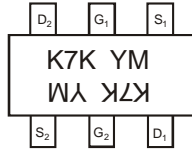

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN601DWK-7	SOT363 (Standard)	3,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT363 (Standard)



K7K = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: L = 2024)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2005	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	S	-	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	I _D	Continuous	305
		Pulsed (Note 6)	800
			mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Notes: 5. Device mounted on FR-4 PCB.
 6. Pulse width ≤ 10μs, duty cycle ≤ 1%.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	1.3 1.5	2.0 3.0	Ω	$V_{GS} = 10V, I_D = 0.5A$ $V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	$ Y_{fs} $	80	—	—	ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}	0.5	0.8	1.4	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	30	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	4.2	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.9	5.0	pF	
Gate Resistance	R_g	—	133	—	Ω	$f = 1MHz, V_{GS} = 0V, V_{DS} = 0V$
Total Gate Charge	Q_g	—	304	—	pC	$V_{GS} = 4.5V, V_{DS} = 10V$ $I_D = 250mA$
Gate-Source Charge	Q_{gs}	—	203	—	pC	
Gate-Drain Charge	Q_{gd}	—	84	—	pC	
Turn-On Delay Time	$t_{D(on)}$	—	3.9	—	ns	$V_{DD} = 30V, V_{GS} = 10V$ $R_g = 25\Omega, I_D = 200mA$
Turn-On Rise Time	t_r	—	3.4	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	15.7	—	ns	
Turn-Off Fall Time	t_f	—	9.9	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

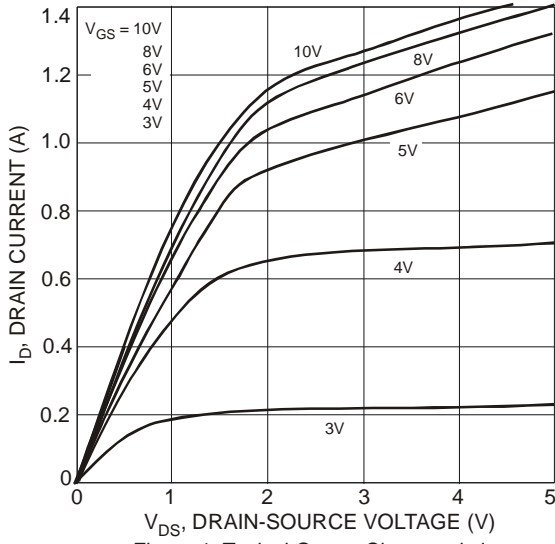


Figure 1 Typical Output Characteristics

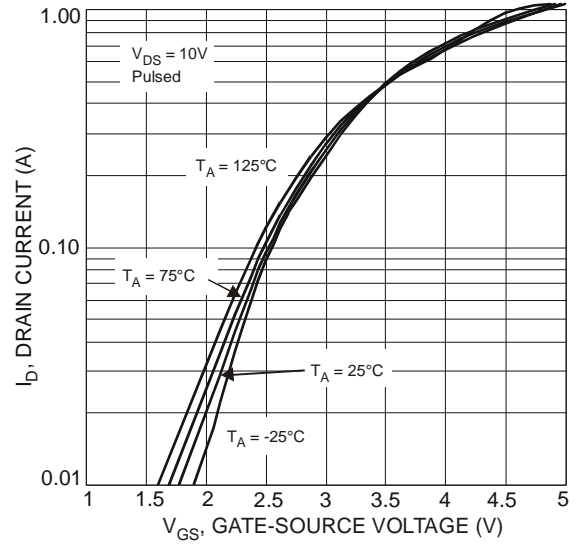


Figure 2 Typical Transfer Characteristics

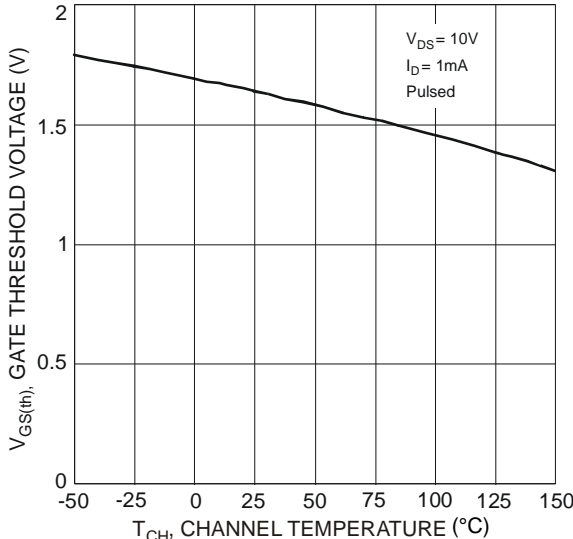


Figure 3 Gate Threshold Voltage vs. Channel Temperature

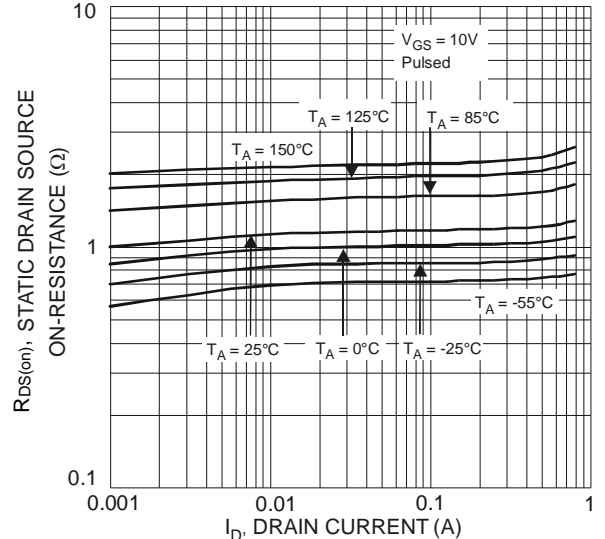


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

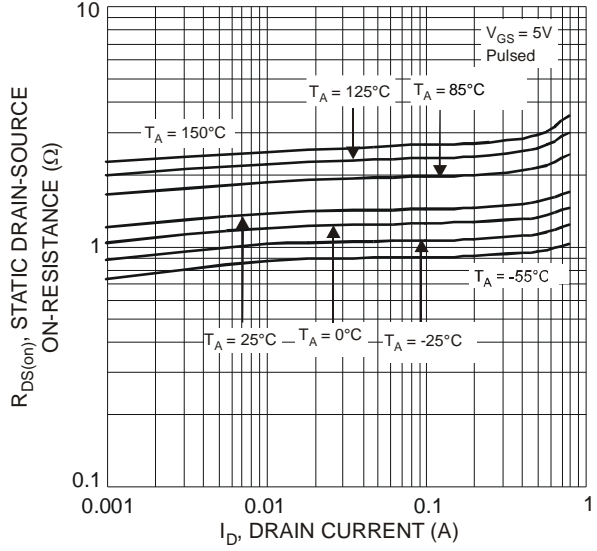


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

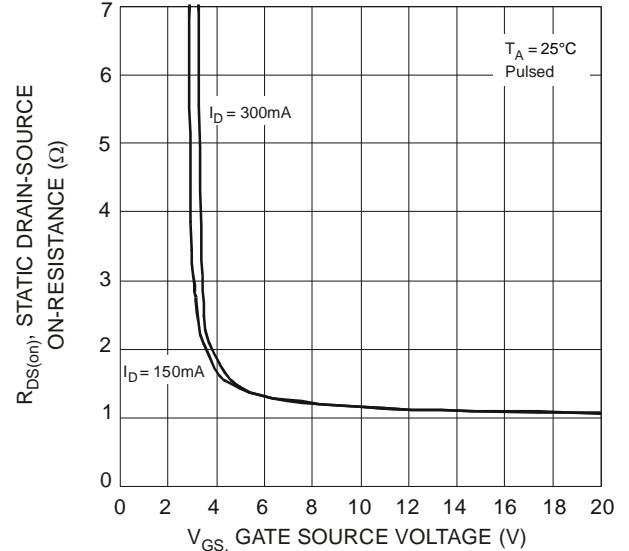


Figure 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

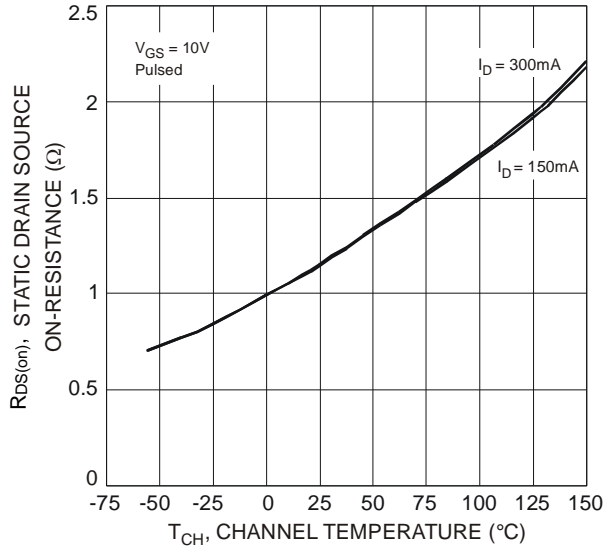


Figure 7 Static Drain-Source On-State Resistance vs. Channel Temperature

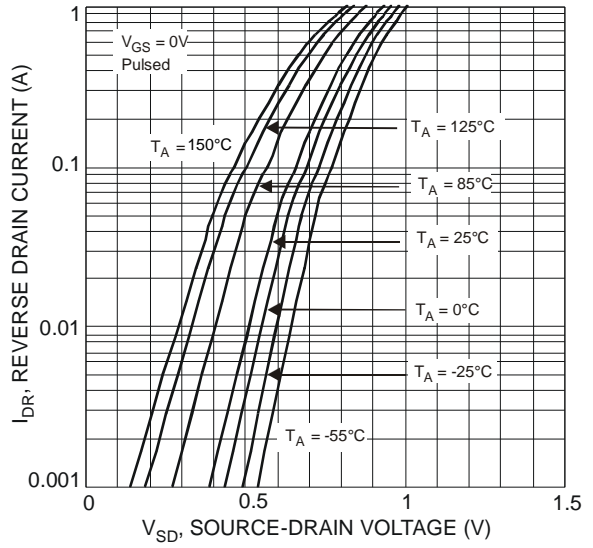


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

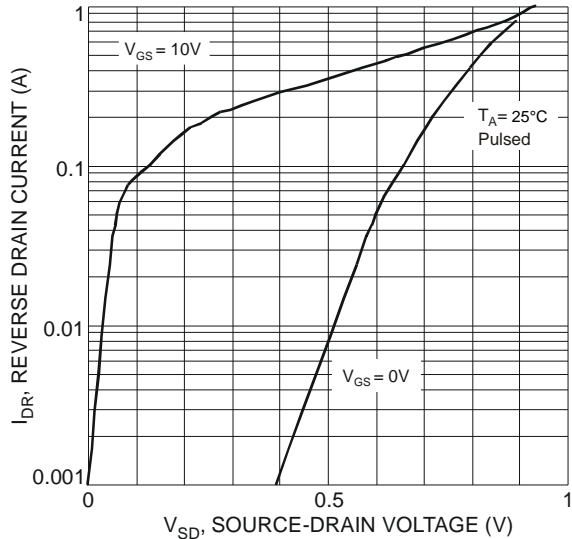


Figure 9 Reverse Drain Current vs. Source-Drain Voltage

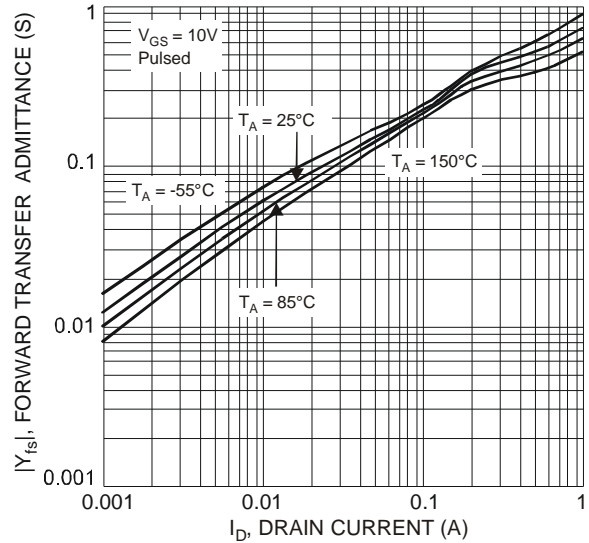


Figure 10 Forward Transfer Admittance vs. Drain Current

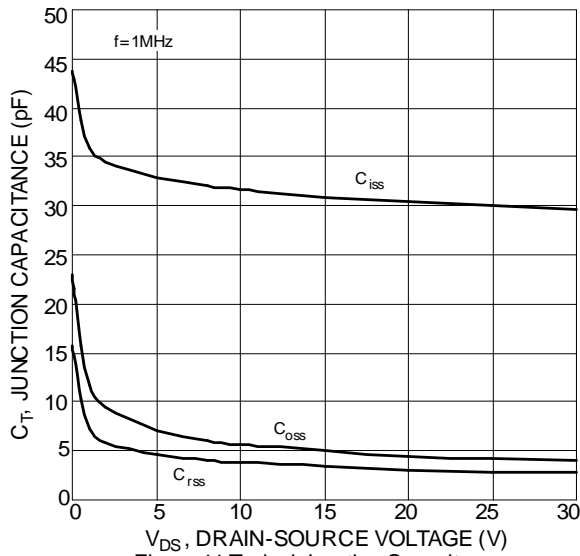


Figure 11 Typical Junction Capacitance

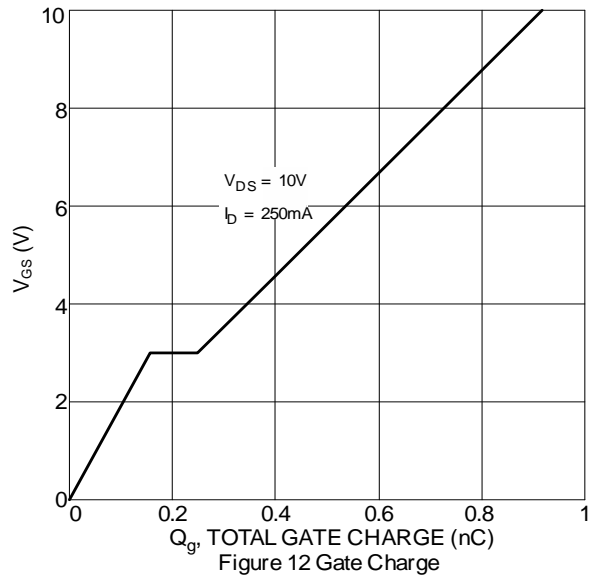


Figure 12 Gate Charge

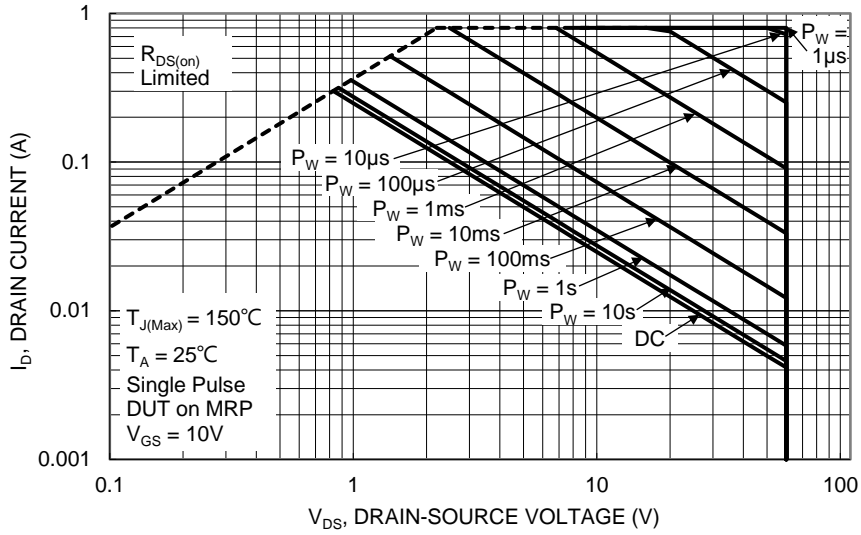


Figure 13 SOA, Safe Operation Area

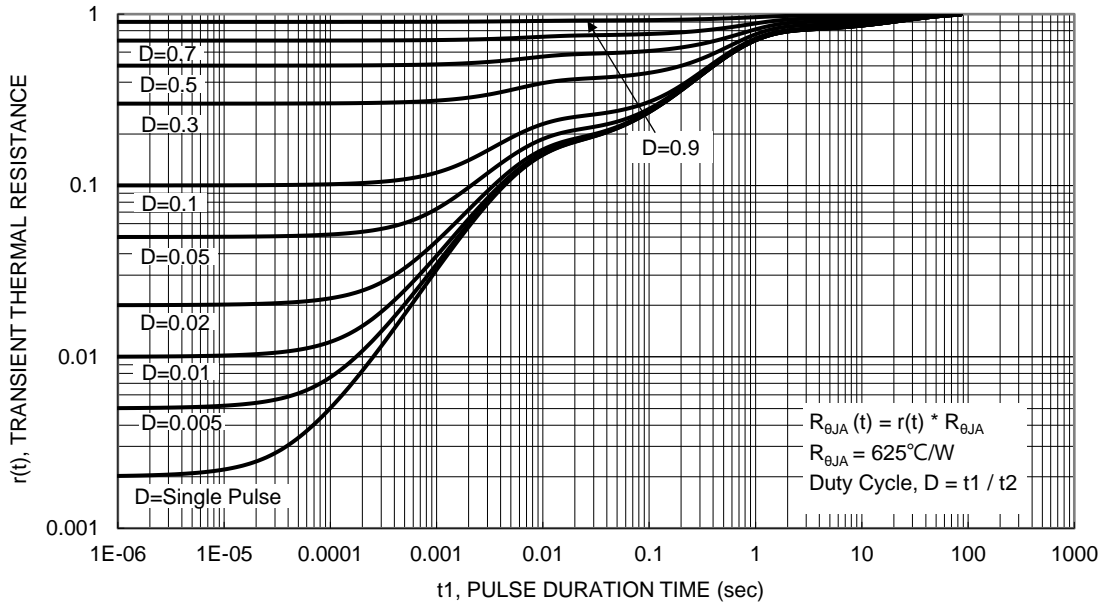
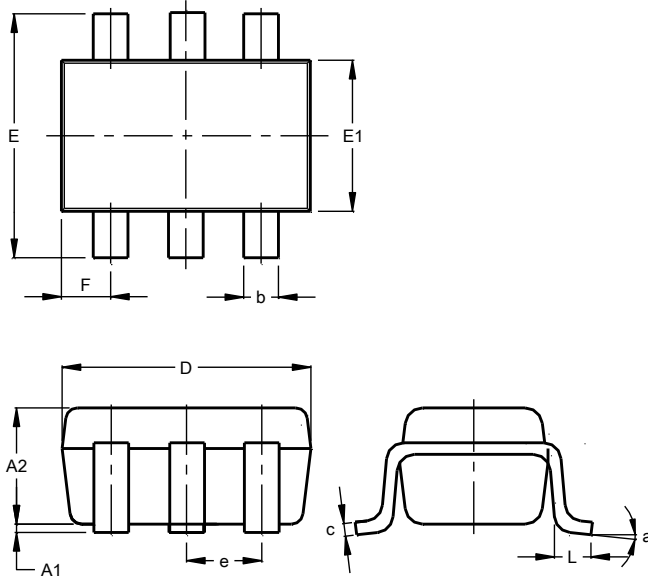


Figure 14 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)

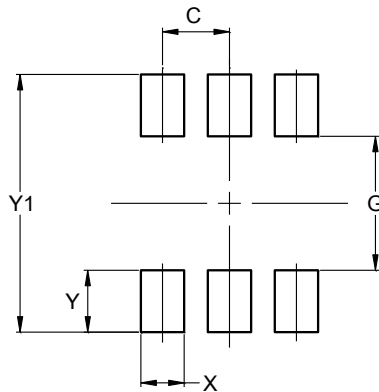


SOT363 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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